

N-channel 600 V, 0.155 Ω typ., 21 A MDmesh™ DM2 Power MOSFET in a PowerFLAT™ 8x8 HV package

Datasheet - production data

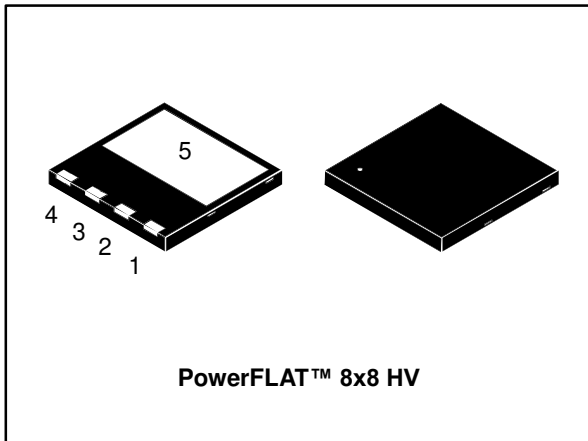
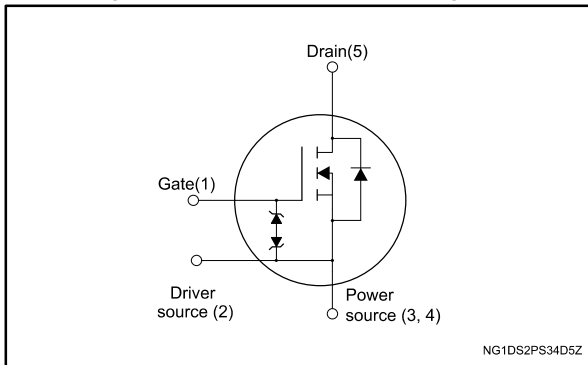


Figure 1: Internal schematic diagram



Features

Order code	V_{DS} @ $T_{Jmax.}$	$R_{DS(on)}$ max.	I_D	P_{TOT}
STL28N60DM2	650 V	0.175 Ω	21 A	140 W

- Fast-recovery body diode
- Extremely low gate charge and input capacitance
- Low on-resistance
- 100% avalanche tested
- Extremely high dv/dt ruggedness
- Zener-protected

Applications

- Switching applications

Description

This high voltage N-channel Power MOSFET is part of the MDmesh™ DM2 fast recovery diode series. It offers very low recovery charge (Q_{rr}) and time (t_{rr}) combined with low $R_{DS(on)}$, rendering it suitable for the most demanding high efficiency converters and ideal for bridge topologies and ZVS phase-shift converters.

Table 1: Device summary

Order code	Marking	Package	Packing
STL28N60DM2	28N60DM2	PowerFLAT™ 8x8 HV	Tape and reel

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1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	± 25	V
$I_D^{(1)}$	Drain current (continuous) at $T_{case} = 25\text{ }^\circ\text{C}$	21	A
	Drain current (continuous) at $T_{case} = 100\text{ }^\circ\text{C}$	14	
$I_{DM}^{(1)(2)}$	Drain current (pulsed)	84	A
$P_{TOT}^{(1)}$	Total dissipation at $T_{case} = 25\text{ }^\circ\text{C}$	140	W
$dv/dt^{(3)}$	Peak diode recovery voltage slope	50	V/ns
$dv/dt^{(4)}$	MOSFET dv/dt ruggedness	50	V/ns
T_{stg}	Storage temperature	-55 to 150	$^\circ\text{C}$
T_j	Operating junction temperature		

Notes:

- (1) The value is limited by package.
 (2) Pulse width limited by safe operating area.
 (3) $I_{SD} \leq 21\text{ A}$, $di/dt \leq 900\text{ A}/\mu\text{s}$, $V_{DD} = 400\text{ V}$, $V_{DS(peak)} < V_{(BR)DSS}$.
 (4) $V_{DS} \leq 480\text{ V}$.

Table 3: Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	0.89	$^\circ\text{C}/\text{W}$
$R_{thj-amb}^{(1)}$	Thermal resistance junction-ambient	45	

Notes:

- (1) When mounted on a 1-inch² FR-4, 2oz Cu board.

Table 4: Avalanche characteristics

Symbol	Parameter	Value	Unit
$I_{AR}^{(1)}$	Avalanche current, repetitive or not repetitive	4	A
$E_{AS}^{(2)}$	Single pulse avalanche energy	350	mJ

Notes:

- (1) Pulse width limited by T_{jmax} .
 (2) starting $T_j = 25\text{ }^\circ\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$.

2 Electrical characteristics

($T_{\text{case}} = 25\text{ °C}$ unless otherwise specified)

Table 5: Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$, $I_D = 1\text{ mA}$	600			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$, $V_{DS} = 600\text{ V}$			1	μA
		$V_{GS} = 0\text{ V}$, $V_{DS} = 600\text{ V}$, $T_{\text{case}} = 125\text{ °C}$			100	μA
I_{GSS}	Gate-body leakage current	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 25\text{ V}$			± 10	μA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$, $I_D = 10.5\text{ A}$		0.155	0.175	Ω

Table 6: Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 100\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0\text{ V}$	-	1500	-	pF
C_{oss}	Output capacitance		-	70	-	
C_{rss}	Reverse transfer capacitance		-	1.6	-	
$C_{oss,eq}^{(1)}$	Equivalent output capacitance	$V_{GS} = 0\text{ V}$, $V_{DS} = 0\text{ to }480\text{ V}$	-	134	-	pF
R_G	Intrinsic gate resistance	$f = 1\text{ MHz}$, $I_D = 0\text{ A}$	-	4.6	-	Ω
Q_g	Total gate charge	$V_{DD} = 480\text{ V}$, $I_D = 21\text{ A}$, $V_{GS} = 10\text{ V}$ (see Figure 15: "Gate charge test circuit")	-	34	-	nC
Q_{gs}	Gate-source charge		-	8	-	
Q_{gd}	Gate-drain charge		-	18.5	-	

Notes:

⁽¹⁾ $C_{oss,eq}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 7: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 300\text{ V}$, $I_D = 10.5\text{ A}$ $R_G = 4.7\text{ }\Omega$, $V_{GS} = 10\text{ V}$ (see Figure 14: "Switching times test circuit for resistive load" and Figure 19: "Switching time waveform")	-	16	-	ns
t_r	Voltage rise time		-	7.3	-	
$t_{d(off)}$	Turn-off delay time		-	53	-	
t_f	Current fall time		-	9.3	-	

Table 8: Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}^{(1)}$	Source-drain current		-		21	A
$I_{SDM}^{(1)(2)}$	Source-drain current (pulsed)		-		84	A
$V_{SD}^{(3)}$	Forward on voltage	$V_{GS} = 0 \text{ V}$, $I_{SD} = 21 \text{ A}$	-		1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 21 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$, $V_{DD} = 100 \text{ V}$ (see Figure 16: "Test circuit for inductive load switching and diode recovery times")	-	140		ns
Q_{rr}	Reverse recovery charge		-	0.5		μC
I_{RRM}	Reverse recovery current		-	7.4		A
t_{rr}	Reverse recovery time	$I_{SD} = 21 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$, $V_{DD} = 100 \text{ V}$, $T_J = 150 \text{ }^\circ\text{C}$ (see Figure 16: "Test circuit for inductive load switching and diode recovery times")	-	309		ns
Q_{rr}	Reverse recovery charge		-	2.6		μC
I_{RRM}	Reverse recovery current		-	16.8		A

Notes:

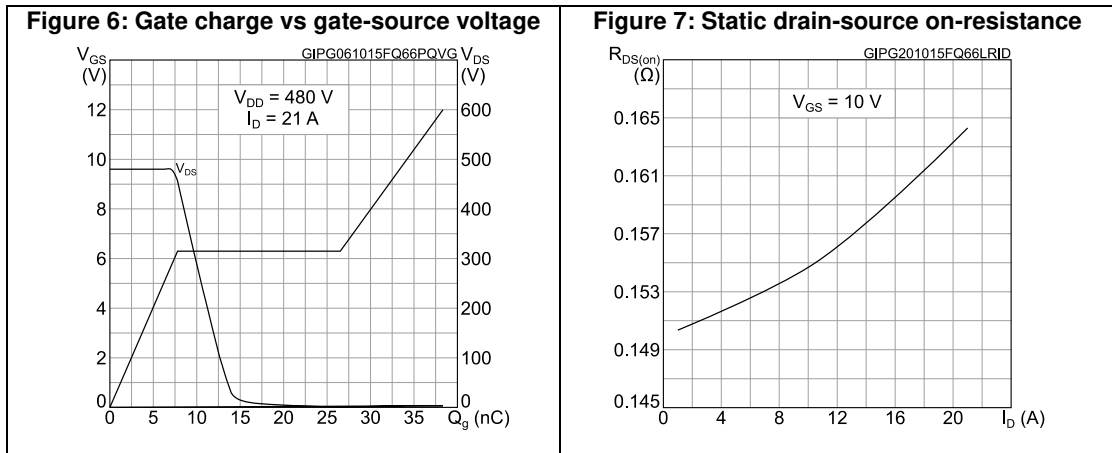
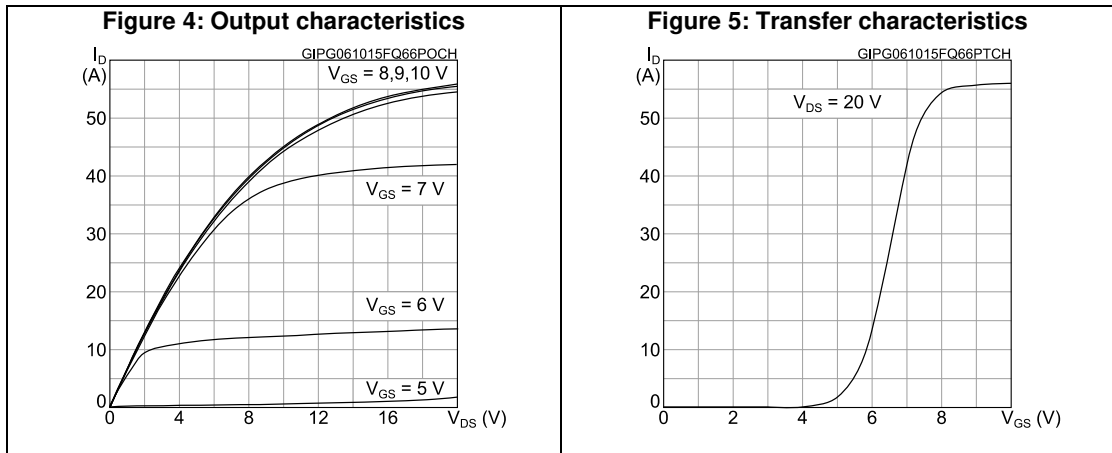
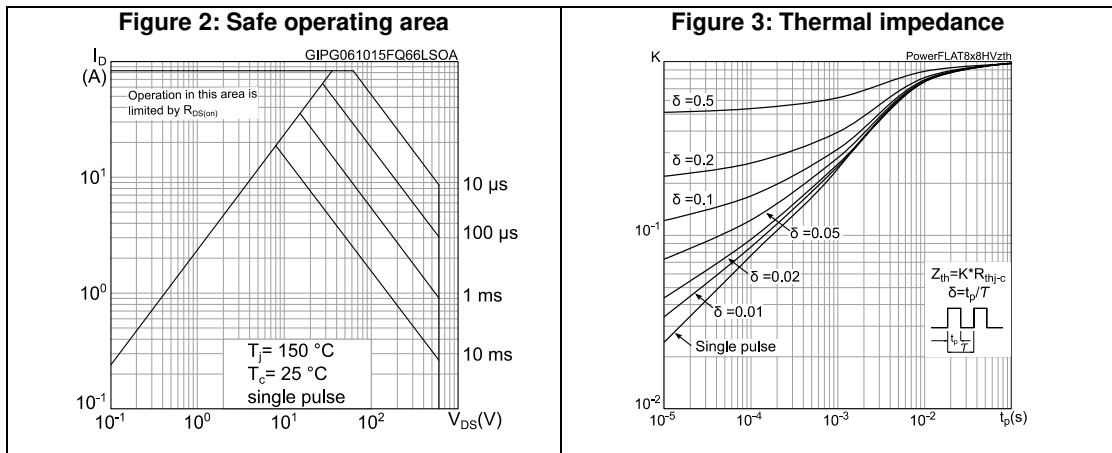
- (1) The value is rated according to $R_{thj-case}$ and limited by package.
(2) Pulse width is limited by safe operating area.
(3) Pulse test: pulse duration = 300 μs , duty cycle 1.5%.

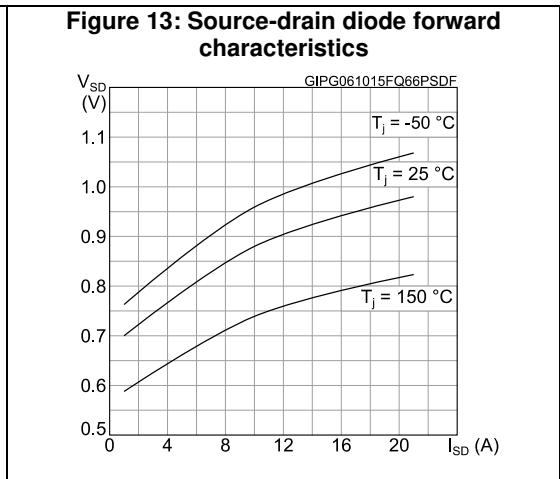
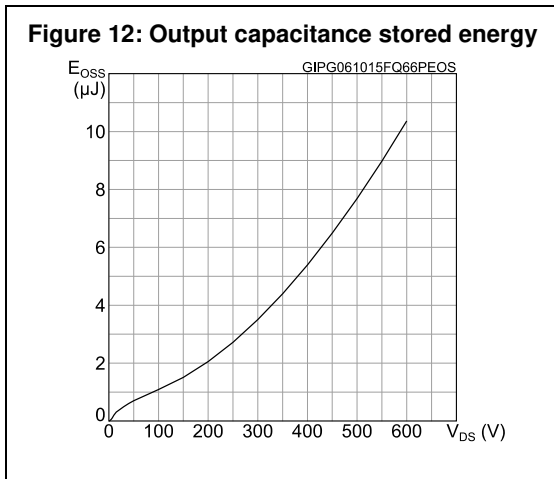
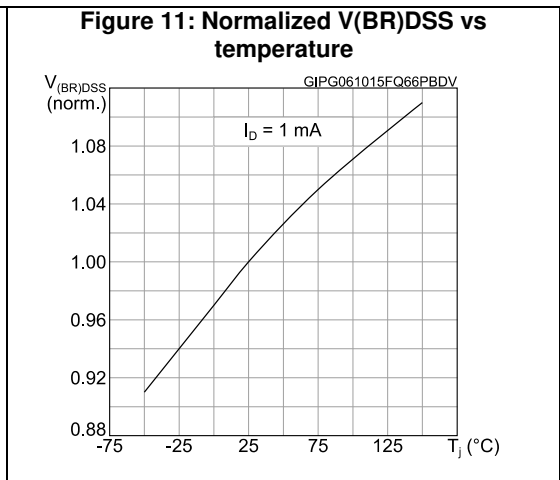
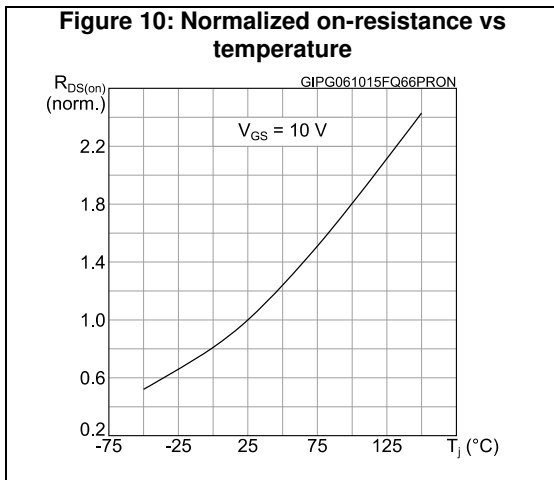
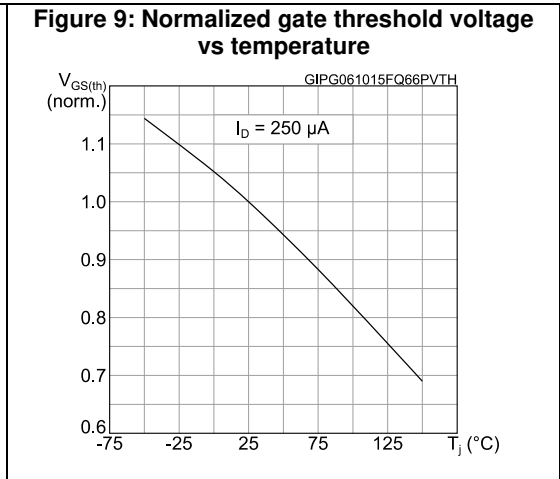
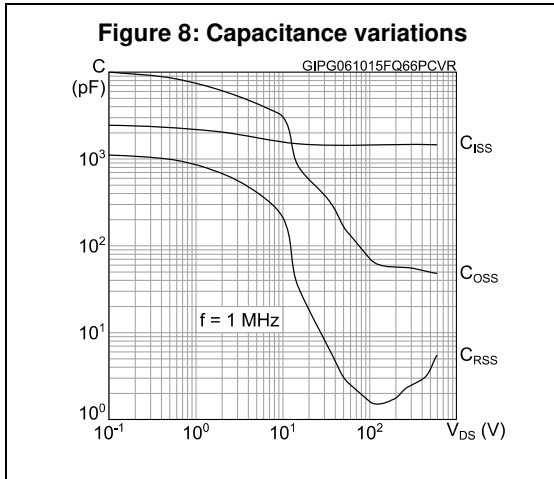
Table 9: Gate-source Zener diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)GSO}$	Gate-source breakdown voltage	$I_{GS} = \pm 1 \text{ mA}$, $I_D = 0 \text{ A}$	± 30	-	-	V

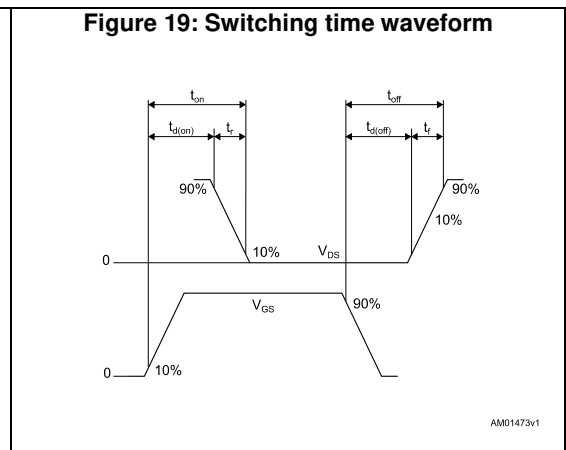
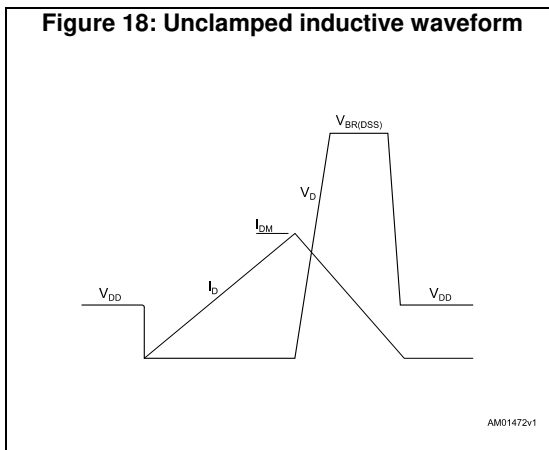
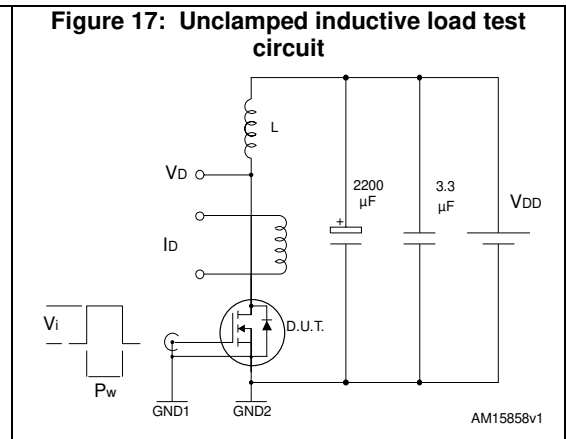
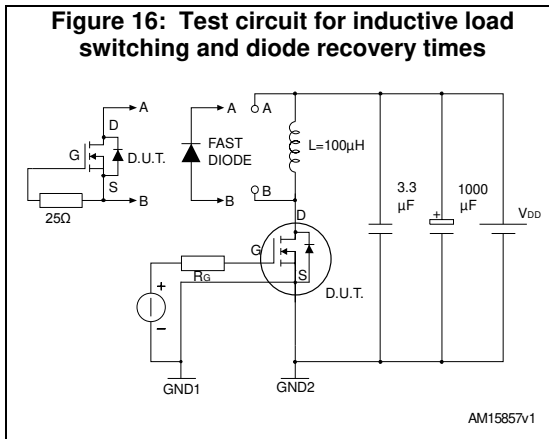
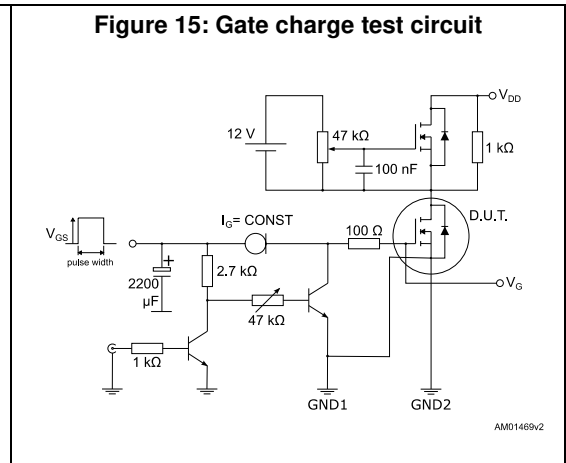
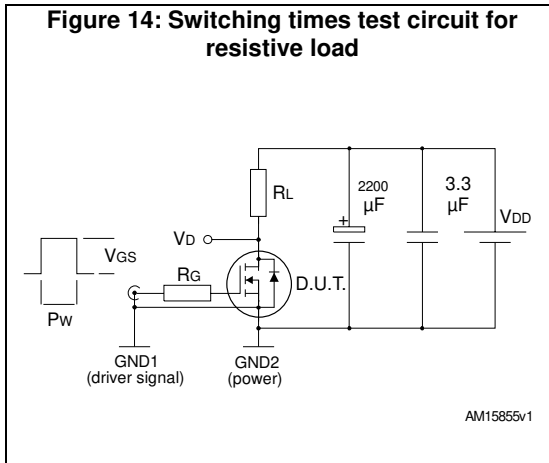
The built-in back-to-back Zener diodes are specifically designed to enhance the ESD performance of the device. The Zener voltage facilitates efficient and cost-effective device integrity protection, thus eliminating the need for additional external componentry.

2.1 Electrical characteristics (curves)





3 Test circuits



4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

4.1 PowerFLAT 8x8 HV package information

Figure 20: PowerFLAT™ 8x8 HV package outline

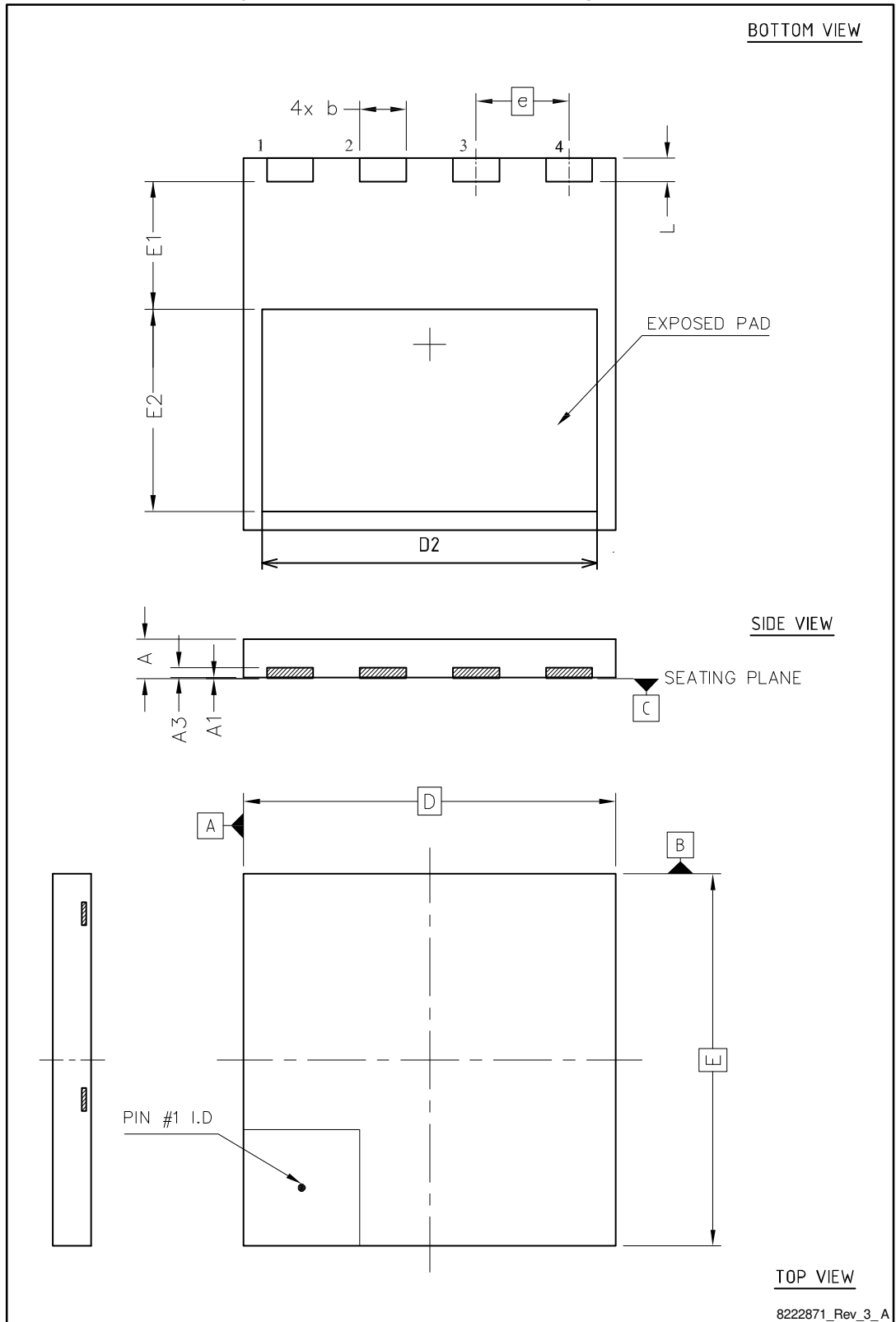
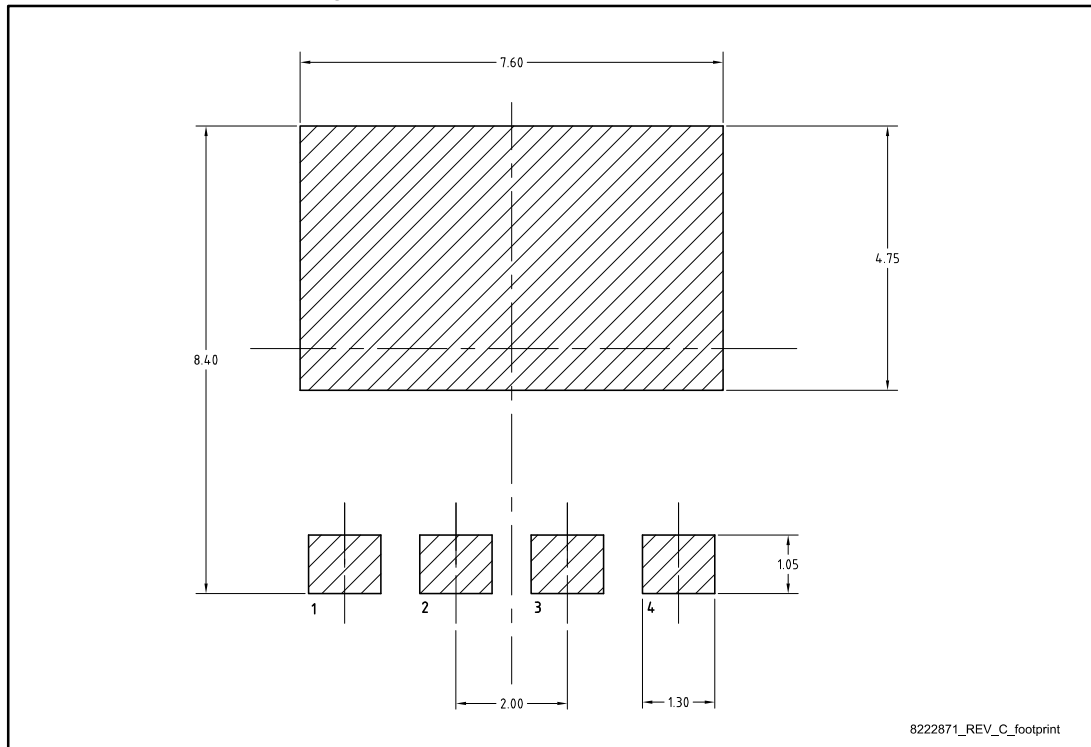


Table 10: PowerFLAT™ 8x8 HV mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.75	0.85	0.95
A1	0.00		0.05
A3	0.10	0.20	0.30
b	0.90	1.00	1.10
D	7.90	8.00	8.10
E	7.90	8.00	8.10
D2	7.10	7.20	7.30
E1	2.65	2.75	2.85
E2	4.25	4.35	4.45
e		2.00	
L	0.40	0.50	0.60

Figure 21: PowerFLAT™ 8x8 HV footprint



All dimensions are in millimeters.

4.2 PowerFLAT 8x8 HV packing information

Figure 22: PowerFLAT™ 8x8 HV tape

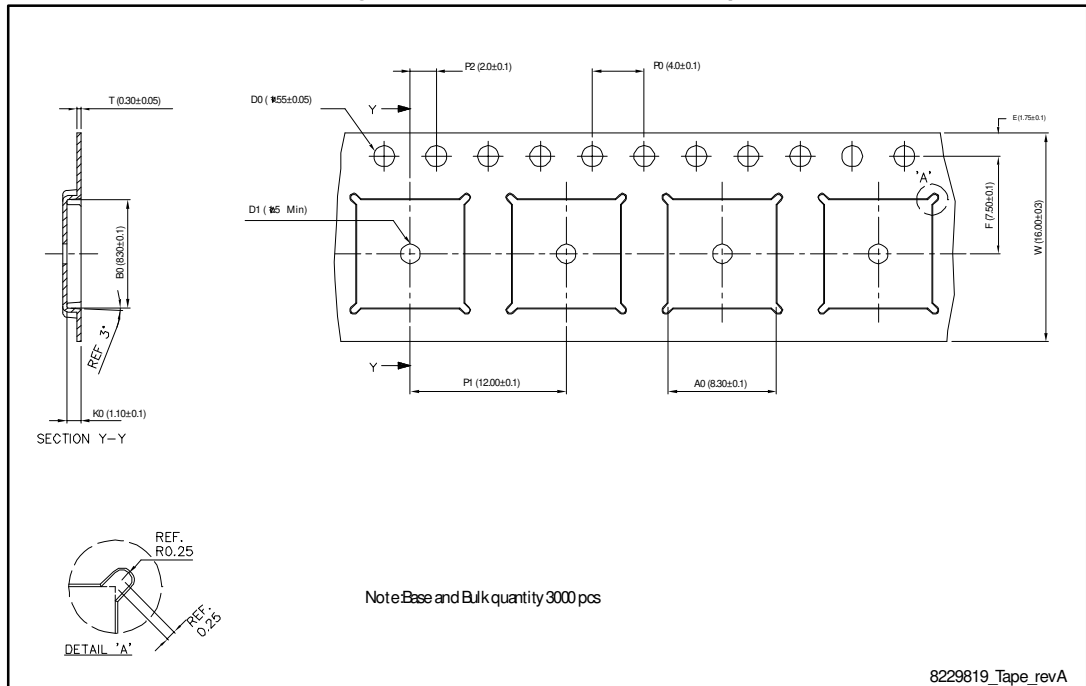
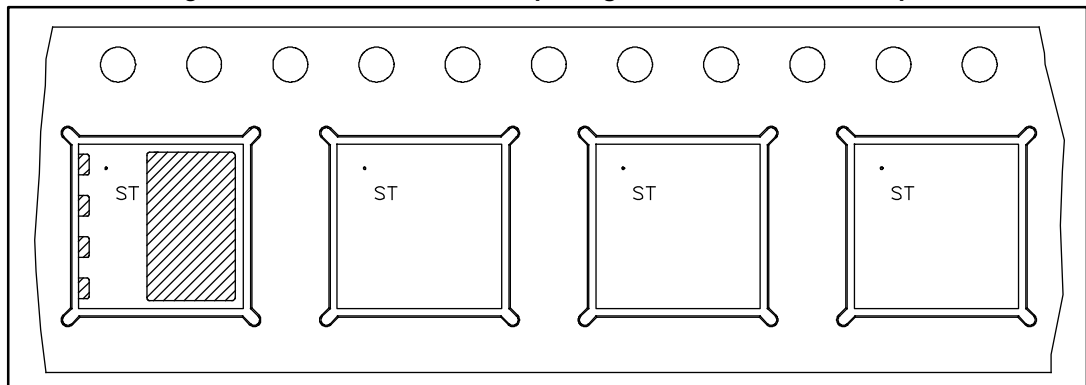


Figure 23: PowerFLAT™ 8x8 HV package orientation in carrier tape



5 Revision history

Table 11: Document revision history

Date	Revision	Changes
08-Aug-2014	1	First release.
16-Oct-2015	2	Text and formatting changes throughout document Datasheet status changed from preliminary to production data In section Electrical ratings: - added table Avalanche characteristics In section Electrical characteristics: - renamed table Static (was On /off states) Added section Electrical characteristics (curves) Updated section Test circuits Updated and renamed section Package information (was Package mechanical data)

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